

INDIAN INSTITUTE OF TECHNOLOGY BOMBAY MATERIALS MANAGEMENT DIVISION Powai, Mumbai 400076

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Detailed Technical Specifications for Power Device Characterization System

1. Power Device Characterization System- Parameter Analyzer (Power device curve tracer/analyser mainframe)

Key Generic Requirements:

- a. The tenderer must provide an installation scheme showing the physical space (footprint) of the item(s) as well as space required for routine access and all installations including related accessories.
- b. The vendor should have installed at least two similar types of systems in centrally funded technical institutes or government research labs. Purchase order (PO) and user list should be provided as supporting evidence.
- c. The compliance sheet should be provided by the vendor. The absence of the compliance sheet may result in the cancellation of the purchase order.
- d. For each compliance, supporting evidence such as manuals and other necessary and supporting documents needs to be provided.
- a. The vendor should have an Indian representative which can take care of the urgent troubleshooting or any queries on an urgent basis.
- e. Installation and training of the system should be demonstrated.

Technical Specifications (Generic):

The primary purpose of the equipment is to measure high voltage and high current data of on-wafer as well as packaged high power devices such as transistors, diodes, IGBTs based on conventional and emerging wide-bandgap semiconductors such as GaN, SiC, Ga₂O₃, diamond etc.

High Voltage and High current Parameter Analyzer

- ii. High Voltage and High current Probe Station
- iii. Accessories

The above components can be from different manufacturers but should be quoted item-wise in a single bid/quotation.

Technical Specifications (Specific):

A. PARAMETER ANALYZER

- The mainframe system should include automated measurement collection and data storage/extraction with latest analysis software. Software upgrades should be assured for the first three years after installation for the mainframe. (Power device curve tracer/analyser mainframe)
- 2. Rack mount kit for Power device curve tracer/analyser mainframe.
 - 3.0m cable
 - 50Hz Line Frequency
- 3. Medium Power Source/Monitor Unit Module
- 4. High Voltage Source Monitor Unit
- 5. Medium Current Source Monitor Unit
- 6. Multi Frequency Capacitance Measurement Unit Module
- 7. Ground Unit with Triax Cable
- **8.** High Voltage Source Monitor Unit Cable (1.5m), Packaged DUT Test Fixture and Associated Accessories, Accessories for instruments and fixtures
- 9. HV Plug connector Panel Mount
- **10.** SHV Cables (3 Nos., Minimum length of 1.5m)
- **11.** Cable for 500A Ultra High Current Probing
- 12. High voltage Bias Tees
- 13. High voltage Bias Tees- STD
- **14.** Protection adapter for High Power Source Monitor Unit (HV-Triaxial output), R-BOX for Power Device Analyser
- 15. HV Triaxial to SHV Adapter
- 16. Ultra-High Current Expander Fixture and Adapter
- 17. Ultra-High Current Expander Fixture and Adapter 001
- 18. Universal R-Box

- 19. Thermocouple, Type K
- **20.** High Voltage Source Monitor Unit Current Expander
- **21.** On-Wafer Gate Charge Measurement Adapter
- **22**.On-site installation and training, Free mainframe calibration should be included for the first three years

Measurement Modules, Numbers and Specifications as given in Table below

No.	Measurement Module	Quantity	Main Specifications
1	Medium Power SMU	1	• Up to 100 V, 100 mA force
			• 10 fA current resolution
2	High Voltage SMU	1	• 1500 V/8 mA;3000 V/4 mA (Pulsed &
			DC)
3	Medium current SMUs	6	• 1 A/30 V (Pulsed); 100 mA/30 V (DC)
4	High Voltage SMU	1	• 1500 V / 2.5 A (Pulsed), 2200 V/ 1.1 A
	Current Expander		(Pulsed)
5	Ultra-High Current	1	• 500 A/60 V (Pulsed), 7.5 kW peak power
	Expander		
6	Multi Frequency CMU	1	• 1 kHz to 5 MHz
			• 0 to ±25 V using internal DC bias
			• 0 to± 3000 V using HVSMU and High
			Voltage Bias-Tee
7	On-Wafer Gate Charge	1	-
	Measurement		

B. PROBE STATION

22	Drol	ne System - EEATLIDES / PENIS	EITS				
	•						
	A) Operator safety and device protection i) Safety category 1 interlocks on a dark box door						
	1	ii) Dedicated chuck design for highest isolation					
	1	iii) Unique high-voltage probe arm design with protected guard area					
		III) Onique nign-voltage probe ann design with protected guard area					
	B) N	B) Measurement accuracy					
		i) Low-noise test environment with EMI-shield concept extended for					
		high-voltage, high-current and high-power applications					
		ii) Seamless integration with measurement equipment (parameter					
		analyser) for best measurement accuracy C) Low cost-of-ownership					
	C) L						
		i) Probe concept allows expansion for other applications such as RF					
		(S-parameter) measurements					
		ii) Unique high-voltage and high-current probe arms designed for					
		standard probe tips and/or replaceable HCP probe tips					
		Shielded Safety Enclosure Moun	ited on Table				
23	POV	VER HANDLING (CHUCK)					
		i) Maximum voltage: 3,000 V (triax) and 10 kV (coax) (Thermal Chuck: capable of 3 kV @ 200°C and 2.5 kV @ 300°C with triax)					
		ii) Maximum current: 100 A (pulsed) iii) Power cord					
	MEA	MEASUREMENT PERFORMANCE – Chuck Triaxial Configuration					
		ick (Triaxial Configuration)					
			Thermal Chuck*				
		Chuck leakage	@ Ambient	@ 300 C			
	i)	a) 10V (typical)	100 fA	200 fA			
	1	b) 3kV (typical)	10 pA	50 pA			
			·				
		Chuck resistance	Ambient				
	ii)	a) Force-Guard (10 V)	25 ΤΩ				
	'''	b) Force-Shield (10 V)	3 ΤΩ				
		c) Guard-Shield (10 V)	500 GΩ				
		Probe leakage	Ambient				
	iii)	a) 0 V (typical)	< 10 fA				
	,	b) 3 kV (typical)	< 1 pA				
	СНІ	JCK SYSTEM	1 + P' ·				
		i) Diameter: 150 mm					
	1	ii) DUT sizes supported: 10 mm x 10 mm, 2 inch, 4 inch and 6 inch					
		wafers					
		iii) Surface: Gold-plated					
		iv) Supported wafer thickness: ≥100 μm					
		v) Configuration: Triaxial design					

	vi) Universal connector for high-voltage and high-current			
	measurements			
	THERMAL CHUCK SYSTEM			
	(i) Flatness: ≤10 μm at ambient, ≤ 30 μm at 200°C			
	(ii) Temperature range: +30°C to 300°C			
	(iii) Resolution: 0.1°C			
	(iv) Accuracy: ± 1°C and ± 1% above 100°C			
	(v) Transition rate (from 30°C to 300°C): ATT: 25 min			
	(vi) Dual triax connector for low leakage and vacuum structures for thin wafers			
	INTERFACE WITH PARAMETER ANALYSER			
24	Complete kit for interfacing with parameter analyser			
25	Test equipment interface to mount parameter analyser accessories and protection adapters- 2 HV Triax measurement Feed-throughs, support for HV-bias-T			
26	Mount for parameter analyser module selector			
27	Test Equipment Interface plate to mount accessories of ultra-high current/ultra-high voltage modules of parameter analyser			
28	VIBRATION ISOLATION PLATFORM			
29	DIGITAL Camera with Monitor			
	1/2.8" CMOS with C-Mount and mounting thread - Capture Resolution on SD-card: Still image: 8.0MP (3840 x 2160) Video: Full HD 1920 x 1080 - Live Display Mode through out USB: 1920 x 1080 (Full HD) @ 30 frames per second or HDMI: 1920 x 1080 (Full HD) @ 60 frames per second - Pixel Size: 2.8 x 2.8 microns Data transfer: HDMI (1080p) and USB 2.0 - SD card slot (maximal: 32 GB) Motic Images Plus 3.0 application software for PC and Mac 24" LCD monitor: HDMI, DisplayPort, VGA inputs - 178° wide-angle view, C-RING, Dust cap, Macro Tube, power supply, 4-dot calibration slide, Cord AC			
	MECHANICAL PERFORMANCE			
	A) Chuck Stage			
	i) Travel: 155 mm x 155 mm (6 inch x 6 inch)			
	ii) Resolution: 5 μm			
	iii) Planarity over 150 mm (6 inch): < 10 μm			
	iv) Load stroke, Y axis: 90 mm			
	v) Z height adjustment range: 10 mm			
	vi) Z contact / separation / load stroke: 0-3 mm adjustable			
	vii) Theta travel (fine): ± 8°			
	P) Diaton			
	B) Platen			

	i) Platen space (typical): Universal platen: space for up to eight positioners			
	ii) Z-Height adjustment range: Maximum 20 mm (depending on configuration)			
	iii) Minimum platen-to-chuck height: 16 mm (universal platen)			
	iv) Separation lift: 200 μm			
	v) Separation repeatability: < 1 μm			
	vi) Vertical rigidity / force: 5 μm / 10 N (0.2 mils / 2.2 lb.)			
	vii) Accessory mounting: Magnetic			
	C) Manual Microscope Stage (On Bridge)			
	i) Travel range: 50 mm x 50 mm (2 inch x 2 inch)			
	ii) Resolution: ≤ 5 μm (0.2 mils)			
	iii) Microscopes: For stereo microscopes with large working distance			
	MICROSCOPE			
	i) Type: Trinocular stereo zoom			
	ii) Zoom range: 1 : 6.7			
	iii) Magnification: 15-100x			
	iv) Camera port For cameras with C-mount			
	v) Illumination: Long life-time LED ring light SAFETY - Interlock			
	i) Interlock: Hardware (safety category 1)			
	ii) Interlock connector: BNC-Twinax (specific interlock cables available			
	for various measurement instruments)			
31	RF positioners, tips and cables (compatible for DC and RF setup)			
	i) 6x Probe posnr, HV, 100tpi, magnetic base, left			
	(ii) HV/HC cables			
	iii) 2x High current probe holder with BNC connection and 5 replaceable probetips (up to 100A current)			
	iv) 6 probe holders with 2 x HVTriax and 3 x HV Coax (3KV) probes			
	v) 2 boxes of 12um and 25um tungsten needles (25 tips per box)			
	vi) 2x East/West RF arms			
	vii) High-voltage tesla chuck connection cable, high voltage chuck connector-Keysight			
	(viii) Hi-current probe holder (500V/10A DC/60A pulse) with operating temperature from -55C to 300C and isolation resistance >100G Phms @500V with cable and positioner capability			
	(ix) Tweezers, Tools and Accessories			
32	One year system warranty and Two years extended warranty			
32	should be included. 3-year Warranty on the probe station and its accessories (except probe tips) should be included			
33	ON-SITE INSTALLATION AND TRAINING			

• Demonstration for onsite acceptance

Complete, integrated installation of the parameter analyser and the probe station should be demonstred on-site. Full capability of the parameter analyser (current, voltage, capacitance and charge measurements) and its various modules and fixtures should be demonstrated on a test device (packaged and on-wafer) supplied by the vendor. Similarly, probe station capability in terms of the chuck temperature range (30 to 300 C) and high current, high voltage capability must be demonstrated.